

### 280MHz single-supply triple video buffer

#### **Features**

- Bandwidth: 280MHz
- 5V single-supply operation
- Internal input DC level shifter
- No input capacitor required
- 6dB internal gain for a matching between 3 channels
- Very low harmonic distortion
- Slew rate: 780V/µs
- Specified for  $150\Omega$  and  $100\Omega$  loads
- Min. and max. data tested during production

#### **Applications**

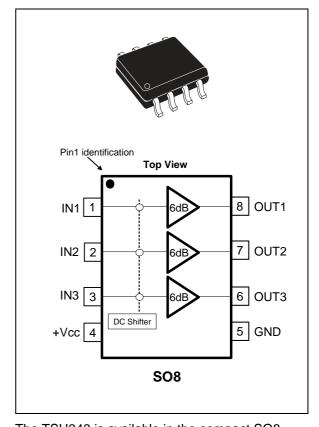
- High-end video systems
- High definition TV (HDTV)
- Broadcast and graphic video
- Multimedia products

#### Description

The TSH343 is a triple single-supply video buffer featuring an internal gain of 6dB and a large 280MHz bandwidth.

The main advantage of this circuit is that its input DC level shifter allows for video signals on  $75\Omega$  video lines without damage to the synchronization tip of the video signal, while using a single 5V power supply with no input capacitor. The DC level shifter is internally fixed and optimized to keep the output video signals between low and high output rails in the best position for the greatest linearity.

This datasheet provides information on using the TSH343 as a Y-Pb-Pr driver for video DAC output on a video line. See the TSH344 datasheet for R-G-B signals.



The TSH343 is available in the compact SO8 plastic package for optimum space-saving.

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# 1 Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings (AMR)

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply voltage <sup>(1)</sup>	6	V
V <sub>in</sub>	Input voltage range (2)	0 to +1.4	V
T <sub>oper</sub>	Operating free air temperature range	-40 to +85	°C
T <sub>stg</sub>	Storage temperature	-65 to +150	°C
T <sub>j</sub>	Maximum junction temperature	150	°C
R <sub>thjc</sub>	SO8 thermal resistance junction to case	28	°C/W
R <sub>thja</sub>	SO8 thermal resistance junction to ambient area	157	°C/W
P <sub>max</sub>	Maximum power dissipation (@T <sub>amb</sub> =25°C) for T <sub>j</sub> =150°C	800	mW
ESD	CDM: charged device model HBM: human body model MM: machine model	2 1.5 200	kV kV V

<sup>1.</sup> All voltage values, except differential voltage, are with respect to network terminal.

Table 2. Operating conditions

Symbol	Parameter	Value	Unit
$V_{CC}$	Power supply voltage	3 to 5.5 <sup>(1)</sup>	V

1. Tested in full production at 0V/5V single power supply.

<sup>2.</sup> The magnitude of input and output voltages must never exceed  $V_{\text{CC}}$  +0.3V.

Electrical characteristics TSH343

## 2 Electrical characteristics

Table 3.  $V_{CC} = +5V$  single supply,  $T_{amb} = 25^{\circ}C$  (unless otherwise specified)

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Symbol	Parameter Test conditions		Min.	Тур.	Max.	Unit		
$ \begin{array}{c} v_{DC} \\ v_{D$	DC perfo	DC performance							
$ \begin{array}{c} \text{temperature}) & -40^{\circ}\text{C} < T_{amb} < +85^{\circ}\text{C} \\ \\ I_{lb} \\ \\ I_{lb} \\ \\ I_{lput} \   \text{timput bias current} \\ \\ R_{lin} \\ \\ I_{lput} \   \text{temperature}) \\ \\ \hline \begin{array}{c} T_{amb}, \   \text{input to GND} \\ \hline \\ -40^{\circ}\text{C} < T_{amb} < +85^{\circ}\text{C} \\ \\ \hline \\ 20.7 \\ \\ \hline \end{array} \begin{array}{c} 20.7 \\ \hline \\ 20.7 \\ \hline \end{array} \begin{array}{c} \mu A \\ \\ \mu A \\ \\ \hline \end{array} \begin{array}{c} R_{lin} \\ \\ I_{lput} \   \text{tresistance} \\ \hline \\ C_{lin} \\ \\ I_{lput} \   \text{capacitance} \\ \hline \\ T_{amb} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ \hline \\ I_{loc} \\ \hline \\ Supply \   \text{current per buffer} \\ \hline \\ I_{loc} \\ I_{loc} \\ \hline \\ I_$		Input DC shift	$R_L = 150\Omega$ , $T_{amb}$	400	600	670			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V <sub>DC</sub>	,	-40°C < T <sub>amb</sub> < +85°C		530		mV		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	l	Input hiss current	T <sub>amb</sub> , input to GND		18.2	35	μА		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	'lb	Input bias current	-40°C < T <sub>amb</sub> < +85°C		20.7		μΛ		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$R_{in}$	Input resistance	T <sub>amb</sub>		4		$G\Omega$		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	C <sub>in</sub>	Input capacitance	T <sub>amb</sub>		1		pF		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		0	no load, input to GND	14.4 18		18	<u> </u>		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	ICC	Supply current per buffer	-40°C < T <sub>amb</sub> < +85°C		14.9		mA		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	PSRR		F = 1MHz		-45		dB		
between inputs of 0.3V and 1V input step from 0.3V to 1V 0.2b 0.8 % MG1 Gain matching between 3 channels Input = 1V 0.5 2 % MG0.3 Gain matching between 3 channels Input = 0.3V 0.5 2 % Dynamic performance and output characteristics	G	DC voltage gain	$R_L = 150\Omega$ , $V_{in} = 1V$	1.92	1.99	2.05	V/V		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	DG		Input step from 0.3V to 1V		0.26	0.8	%		
	MG <sub>1</sub>	Gain matching between 3 channels	Input = 1V		0.5	2	%		
	MG <sub>0.3</sub>	Gain matching between 3 channels	Input = 0.3V		0.5	2	%		
	Dynamic	performance and output characteris	tics						
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	P.u.	-3dB bandwidth		160	280		MUz		
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	ЬW	Gain flatness @ 0.1dB			65		IVITIZ		
SR Slew rate $^{(3)}$ Input step from 0V to 1V, $_{R_L} = 150Ω$ 780 V/μs  V <sub>OH</sub> High level output voltage $V_{\text{in DC}} = +1.5V$ , $R_L = 150Ω$ 3.7 3.9 V  V <sub>OL</sub> Low level output voltage $R_L = 150Ω$ 40 mV  Output current $V_{\text{out}} = 2V$ , $V_{\text{amb}}$ 45 90 mA	FPBW	Full power bandwidth	$V_{out} = 2V_{p-p}, V_{ICM} = 0.5V,$ $R_L = 150\Omega$	130	200		MHz		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	D	Delay between each channel <sup>(2)</sup>	0 to 30MHz		0.5		ns		
$V_{OL}  \text{Low level output voltage} \qquad R_L = 150\Omega \qquad \qquad 40 \qquad \text{mV}$ $V_{Out} = 2\text{V}, \ T_{amb} \qquad 45 \qquad 90 \qquad \text{mA}$ $-40^{\circ}\text{C} < T_{amb} < +85^{\circ}\text{C} \qquad 82 \qquad \qquad \text{mA}$	SR	Slew rate (3)		500	780		V/µs		
	V <sub>OH</sub>	High level output voltage	$V_{\text{in DC}} = +1.5 \text{V}, R_{\text{L}} = 150 \Omega$	3.7	3.9		V		
Output current  Output current  -40°C < T <sub>amb</sub> < +85°C  82	V <sub>OL</sub>	Low level output voltage	$R_L = 150\Omega$		40		mV		
I <sub>OUT</sub> -40°C < T <sub>amb</sub> < +85°C 82		Output current	V <sub>out</sub> = 2V, T <sub>amb</sub>	45	90		mΛ		
Output short-circuit current (I <sub>source</sub> ) 100 mA	$I_{OUT}$	Output carrent	-40°C < T <sub>amb</sub> < +85°C		82		IIIA		
		Output short-circuit current (I <sub>source</sub> )			100		mA		

Table 3.  $V_{CC} = +5V$  single supply,  $T_{amb} = 25^{\circ}C$  (unless otherwise specified) (continued)

	CC 5 11 37 allib	· · · · · · · · · · · · · · · · · · ·		<i>,</i> ,			
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
Noise an	Noise and distortion						
		$F = 100kHz, R_{IN} = 50\Omega$		29		nV/√Hz	
eN	Total input voltage noise	10kHz to 30MHz 10kHz to 100MHz		158 290		μVrms	
HD2	2nd harmonic distortion	$V_{\text{out}} = 2V_{\text{p-p}}, R_{\text{L}} = 150\Omega$ F= 10MHz F= 30MHz		-58 -45		dBc	
HD3	3rd harmonic distortion	$V_{\text{out}} = 2\text{Vp-p}, R_{\text{L}} = 150\Omega$ F= 10MHz F= 30MHz		-72 -50		dBc	

<sup>1.</sup> See Figure 28 and Figure 29.

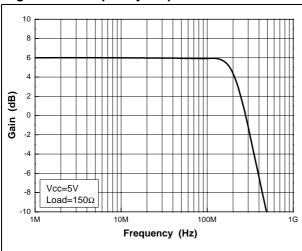
<sup>2.</sup> See Figure 30 and Figure 31.

<sup>3.</sup> Non-tested value, guaranteed by design.

Electrical characteristics TSH343

Figure 1. Frequency response

Figure 2. Gain flatness



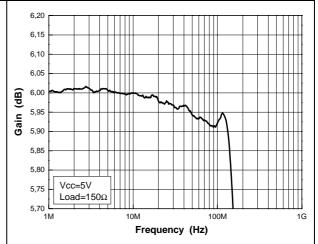
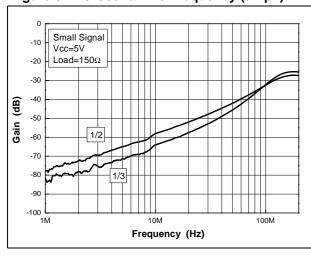


Figure 3. Cross-talk vs. frequency (amp1)

Figure 4. Cross-talk vs. frequency (amp2)



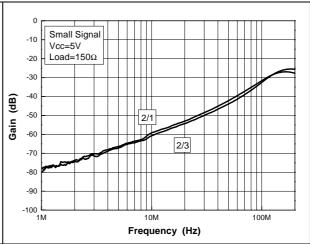
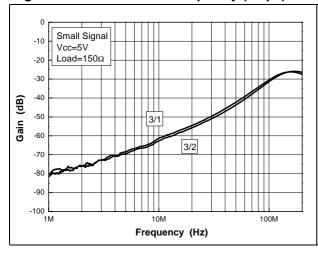


Figure 5. Cross-talk vs. frequency (amp3)

Figure 6. Input noise vs. frequency



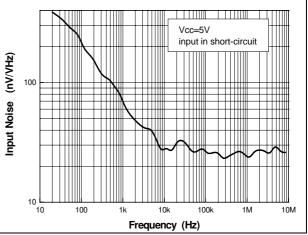
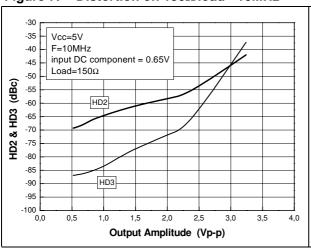


Figure 7. Distortion on  $150\Omega$  load - 10MHz

Figure 8. Distortion on  $100\Omega$  load - 10MHz



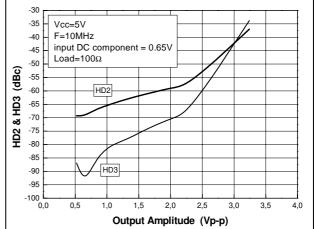
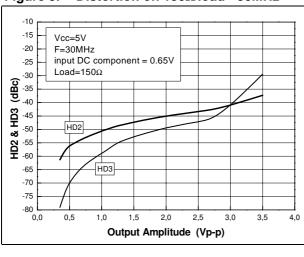


Figure 9. Distortion on 150 $\Omega$  load - 30MHz

Figure 10. Distortion on  $100\Omega$  load - 30MHz



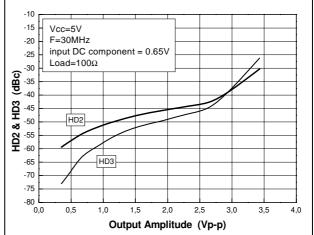
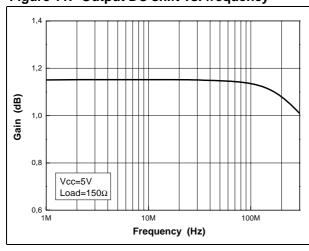
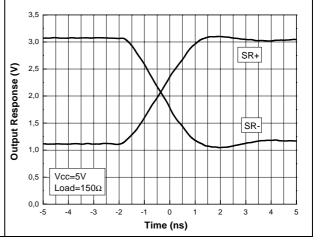


Figure 11. Output DC shift vs. frequency

Figure 12. Slew rate





Electrical characteristics TSH343

Figure 13. Reverse isolation vs. frequency

Figure 14. Bandwidth vs. temperature

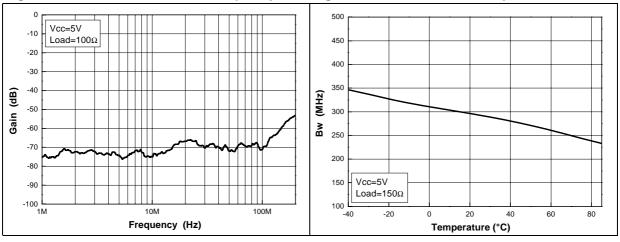


Figure 15. Quiescent current vs. supply

Figure 16. Input DC shift vs. temperature

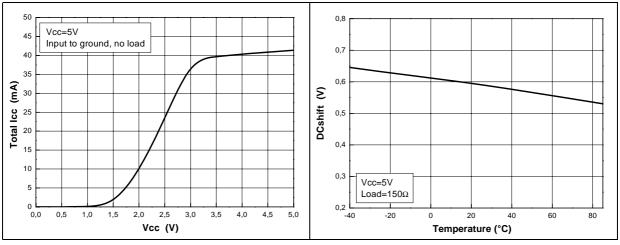
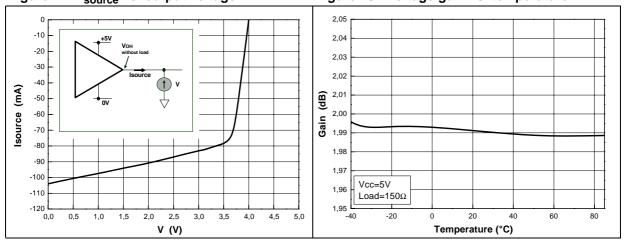


Figure 17.  $I_{\text{source}}$  vs. output voltage

Figure 18. Voltage gain vs. temperature



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Figure 19.  $I_{bias}$  vs. temperature

Figure 20. Gain deviation vs. temperature

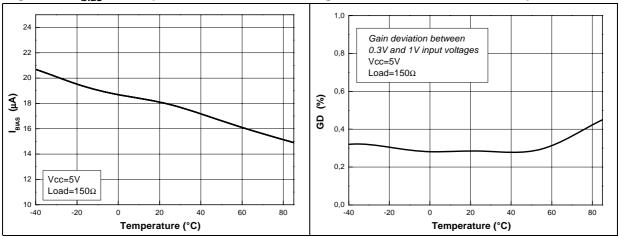


Figure 21. Supply current vs. temperature

Figure 22. Output current vs. temperature

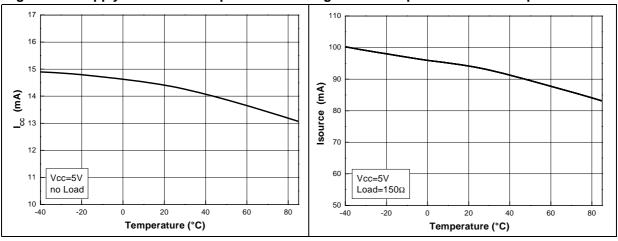
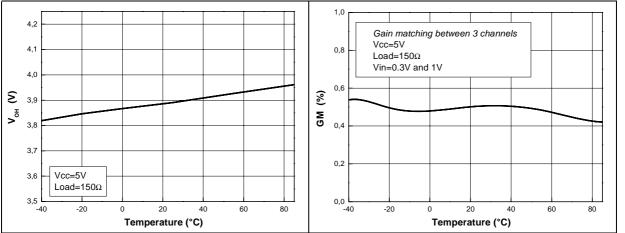


Figure 23. Output higher rail vs. temperature

Figure 24. Gain matching vs. temperature



### 3 Application information

### 3.1 Using the TSH343 to drive Y-Pb-Pr video components

Figure 25. Shapes of video signals coming from DACs

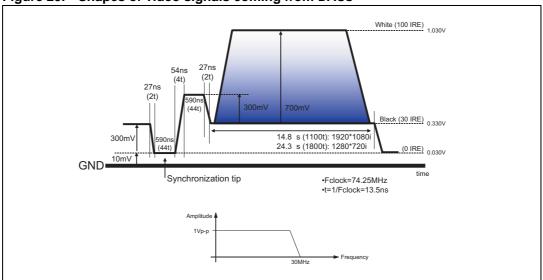
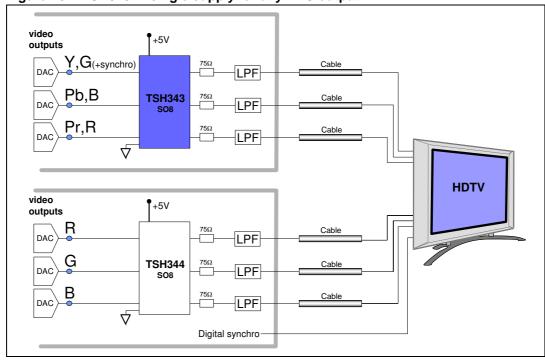


Figure 26. TSH343 in single supply for any DAC output



See the TSH344 datasheet on st.com for more information. It is possible to drive RGB signals with the TSH344.

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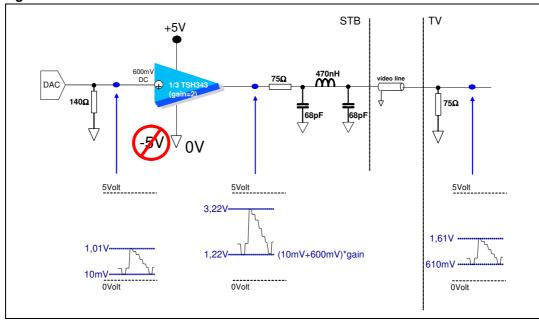


Figure 27. Detailed view of one TSH343 channel

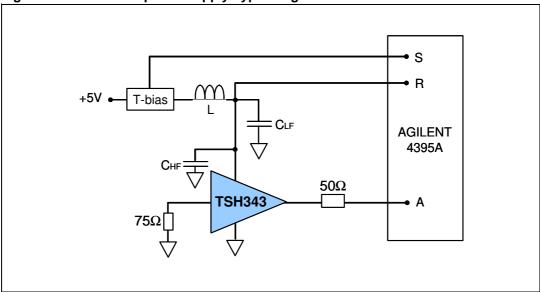
Because of the shape of the signal shown in *Figure 25*, we use a very low output rail triple high-speed buffer. The TSH343 supplied in 5V single power supply, features a low output rail of 40mV on 150-ohm load. The TSH343 is used to drive high definition video signals up to 30MHz on 75-ohm video lines. It is dedicated to driving YPbPr signals where the synchronization tip—close to zero volt—is included in the Y signal.

Figure 27 shows a solution used on the STMicroelectronics reference design of STi7100 or STi7200 where the DAC output is loaded by  $140\Omega$  and the bottom of the synchronization tip is set at 10mV. Using the TSH343, an internal input DC value of 600mV is added to the video signal in order to shift the bottom from 10mV to 610mV. The shift is not based on the average of the signal, but is an analog summation of a DC component to the video signal. Therefore, no input capacitors are required which provides a real advantage in terms of cost and board space.

The internal gain of 2 obtained makes it possible to remove two resistors on the BOM. To avoid any perturbation on matching from the DACs output impedance along a large band of 30MHz in HD, a discrete reconstruction filtering is implemented after the driver. This filter is matched on 75-ohms. Note that the TSH343 cannot be AC output coupled (it cannot sink an output current, therefore it is not possible to implement an output series capacitor).

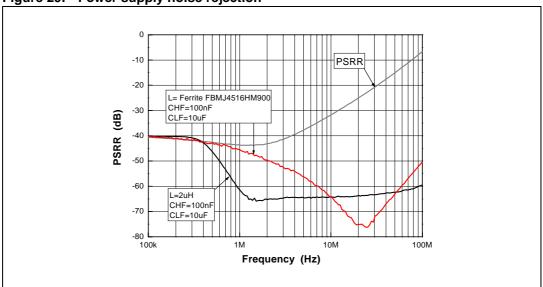
#### 3.2 PSRR and improvement of power supply noise rejection

Figure 28. Circuit for power supply bypassing



*Figure 29* shows how the power supply noise rejection evolves versus frequency depending on how carefully the power supply decoupling is achieved.

Figure 29. Power supply noise rejection



Criteria for choosing the ferrite:

- In DC, the resistance (R) of the ferrite must be as low as possible to keep +5V power supply on the chip.
- In AC, along a 30MHz bandwidth (HD spectrum), the equivalent impedance (Z=R+jX)
  must be as high as possible to optimize rejection of the noise generated by the power
  supply.

#### 3.3 Delay between channels

Vin  $75\Omega$   $75\Omega$  Cable  $75\Omega$   $75\Omega$  Cable  $75\Omega$   $75\Omega$ 

Figure 30. Measurement of the delay between each channel

The delay between each video component is an important aspect in high definition video systems. To properly drive the three video components without any relative delay, the TSH343 dice layout has a very symmetrical geometry. The effect is direct on the synchronization of each channel, as shown in *Figure 31*. There is no delay between channels when the same  $V_{in}$  signal is applied on the three inputs. Note that the delay between the inputs and the outputs is 4ns.

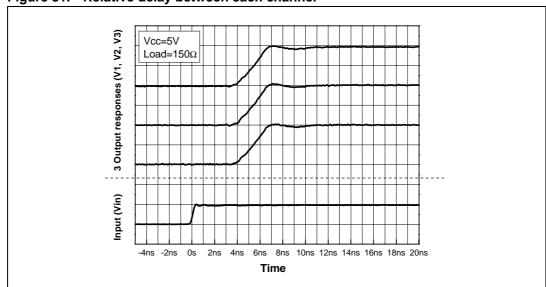


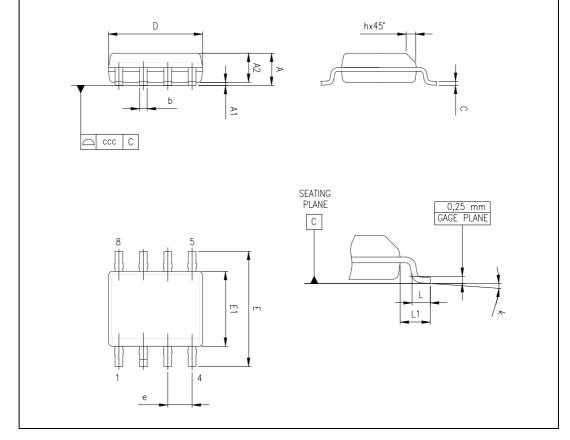
Figure 31. Relative delay between each channel

### 4 Package mechanical data

In order to meet environmental requirements, STMicroelectronics offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an STMicroelectronics trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>.

Figure 32. SO-8 package

			Dime	nsions		
Ref.	Millimeters					
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
С	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
Е	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
е		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	1°		8°	1°		8°
ccc			0.10			0.004



Ordering information TSH343

# **5** Ordering information

Table 4. Order codes

Part number	Temperature range Package		Packing	Marking	
TSH343ID	-40°C to +85°C	SO-8	Tube	TSH343I	
TSH343IDT	-40 0 10 403 0	30-0	Tape & reel	TSH343I	

# 6 Revision history

Table 5. Document revision history

Date	Revision	Changes
1-Dec-2005	1	First release of datasheet.
2-Jan-2006	2	Capa-load option paragraph deleted on page 11.
10-Jul-2006	3	Application information.
7-Mar-2007	4	Max limit for input DC shift reduced from 800mV to 670mV.  Updated Section 3.2: PSRR and improvement of power supply noise rejection on page 12.

TSH343 Revision history

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